

**REPLACEMENT PAGE**

Please replace page 20 of the original application with the corresponding  
Amended Sheet under Article 34.

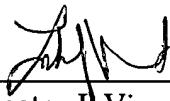
REMARKS

If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: September 15, 2006



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50. A semiconductor device as claimed in any one of claims 43 to 49, wherein the thermally conductive metal is copper and the epitaxial layers comprise multiple GaN-related epitaxial layers.
- 5 51. A semiconductor device as claimed in any one of claims 43 to 50, wherein the semiconductor device is selected from the group consisting of: a light emitting device, and a transistor device.
- 10 52. A semiconductor device as claimed in any one of claims 43 to 50, wherein the second ohmic contact layer is selected from the group consisting of: blank, and patterned.
- 15 53. A semiconductor device fabricated by the method of any one of claims 1 to 42.